



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	200A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	2.9 mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	3.9 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split Gate Trench MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$

-0 Flammability Rating

alogen Free

Applications

Isolated DC-DC Converters
Motor control
Invertors

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current ^A	I_D	$T_C=25$	200
		$T_C=100$	125
Pulsed Drain Current ^B	I_{DM}	600	A
Avalanche energy ^C	EAS	506	mJ
Total Power Dissipation ^D	P_D	260	W
Thermal Resistance Junction-to-Case	R_{JC}	0.48	/ W
Thermal Resistance Junction-to-Ambient ^E	R_{JA}	28	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 +150	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB200G06C	F2	YJB200G06C				

Typical Performance Characteristics

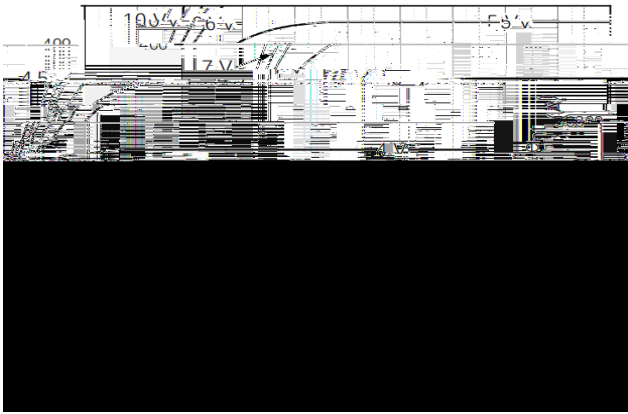


Figure1. Output Characteristics



Figure2. Transfer Characteristics

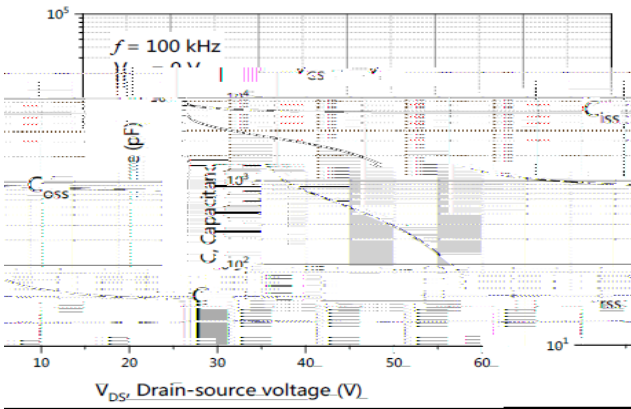


Figure3. Capacitance Characteristics

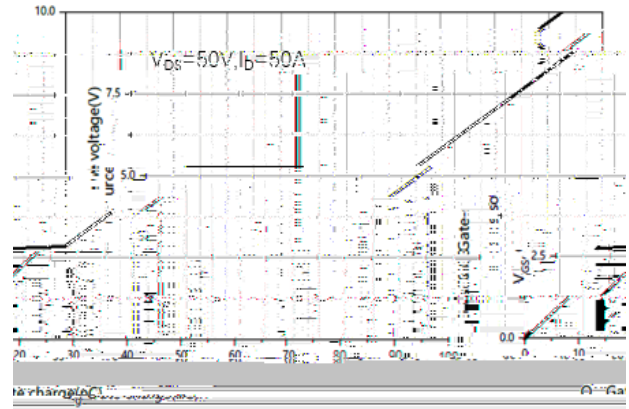


Figure4. Gate Charge



Figure5. Drain-Source on Resistance

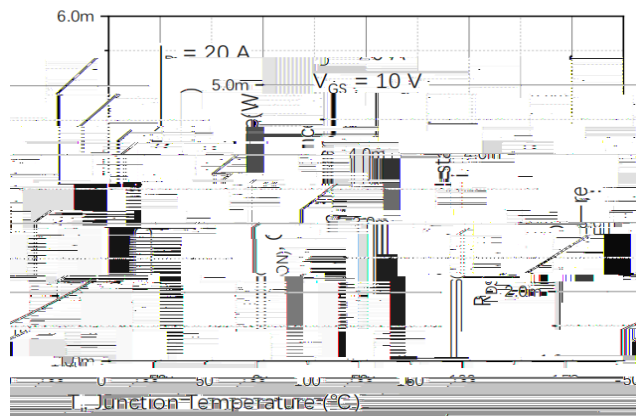


Figure6. Drain-Source on Resistance

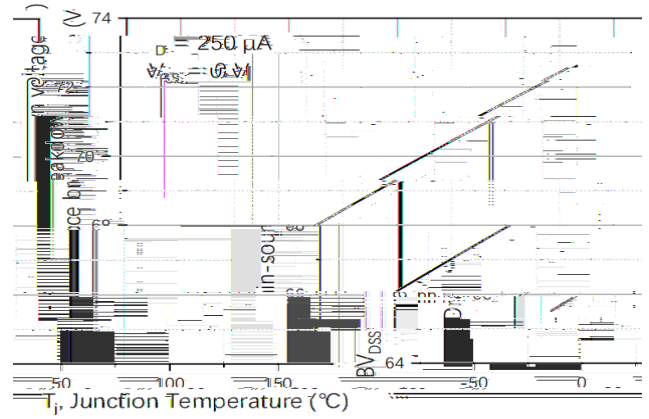


Figure8. Drain-source breakdown voltage

Figure7. Safe Operation Area

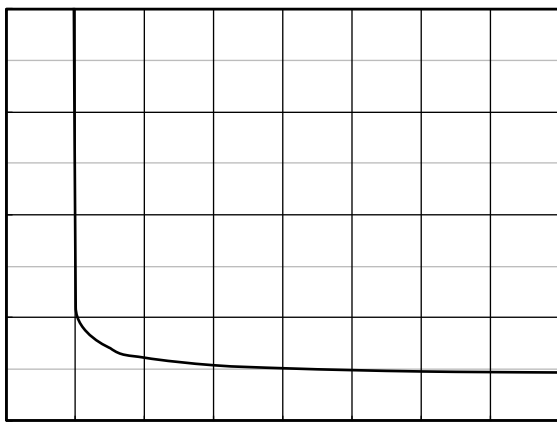


Figure9. On-Resistance vs Gate to Source Voltage

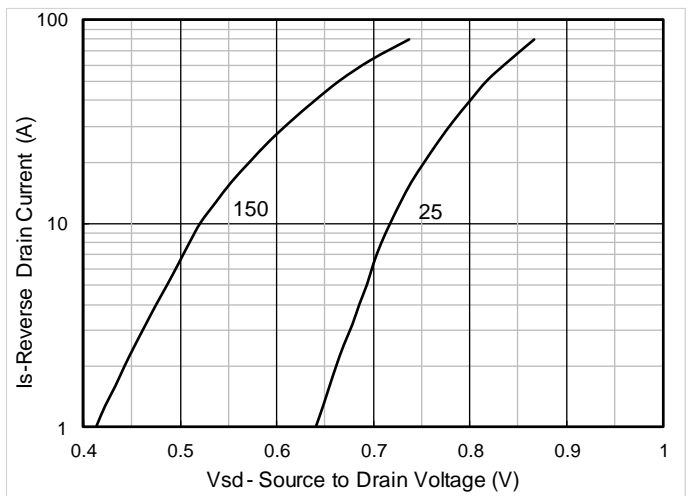


Figure10. Forward characteristics of reverse diode

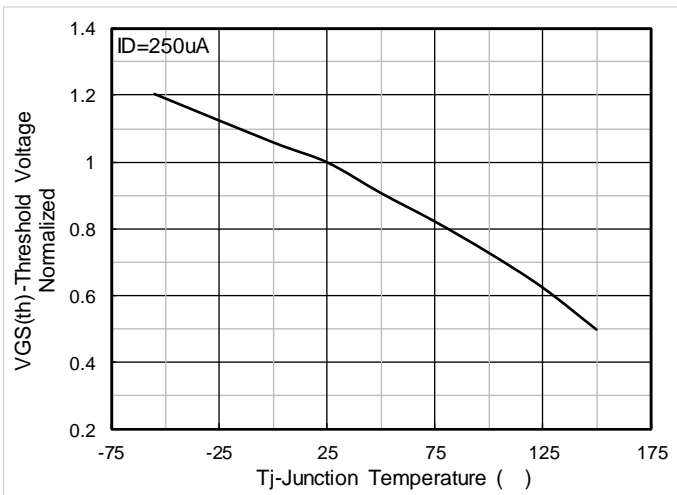


Figure11. Normalized Threshold voltage

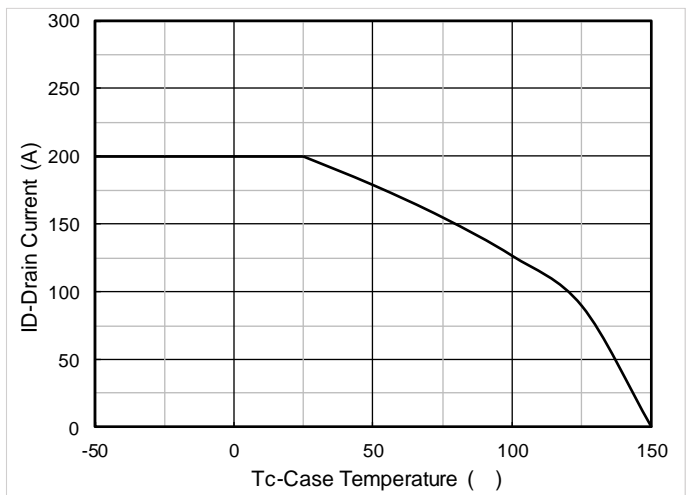


Figure12. Current dissipation



TO-263-HY Package information

SYML	MIN.	
A2		
b2	0.050	
c		
c2		
D2		
E		
E1		



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or 6(p)-3(r)13(o)-3(v)7(e)-3()-41(re)-3()-54(fo)-5(r)-41(a)-3(n)-3(y)7()5